

4 active layer; and

5 a second pair of marks straddling said active layer, said second pair of marks located
6 at a further distance from said active layer than said first pair of marks,

7 wherein said second pair of marks align with a pair of substrate side marks formed at
8 a position opposed to said second pair of marks, and

9 wherein said first pair of marks comprises lines formed on an upper portion of said
10 active layer.

31. (Amended) A semiconductor laser diode chip to be mounted on a substrate for an
optical module, comprising:

an active layer;

a positioning-type mark in a vicinity of said active layer; and

a measurement-type mark located between said active layer and said positioning-type
mark,

wherein said positioning-type mark is constructed by a thin line formed on an upper
portion of said active layer.